

Mikael Å-stling

List of Publications by Year in descending order

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420
papers

9,127
citations

66343

42
h-index

71685

76
g-index

430
all docs

430
docs citations

430
times ranked

8625
citing authors

#	ARTICLE	IF	CITATIONS
1	Efficient Inkjet Printing of Graphene. Advanced Materials, 2013, 25, 3985-3992.	21.0	425
2	Electromechanical Piezoresistive Sensing in Suspended Graphene Membranes. Nano Letters, 2013, 13, 3237-3242.	9.1	332
3	Metal Silicides in CMOS Technology: Past, Present, and Future Trends. Critical Reviews in Solid State and Materials Sciences, 2003, 28, 1-129.	12.3	323
4	Scalable Fabrication and Integration of Graphene Microsupercapacitors through Full Inkjet Printing. ACS Nano, 2017, 11, 8249-8256.	14.6	280
5	Resistive graphene humidity sensors with rapid and direct electrical readout. Nanoscale, 2015, 7, 19099-19109.	5.6	252
6	Residual Metallic Contamination of Transferred Chemical Vapor Deposited Graphene. ACS Nano, 2015, 9, 4776-4785.	14.6	250
7	SiC power devices — Present status, applications and future perspective. , 2011, , .		223
8	A Graphene-Based Hot Electron Transistor. Nano Letters, 2013, 13, 1435-1439.	9.1	215
9	Inkjet Printing of MoS ₂ . Advanced Functional Materials, 2014, 24, 6524-6531.	14.9	210
10	Vertical Graphene Base Transistor. IEEE Electron Device Letters, 2012, 33, 691-693.	3.9	141
11	Inkjet printed highly transparent and flexible graphene micro-supercapacitors. Nanoscale, 2017, 9, 6998-7005.	5.6	139
12	A Comprehensive Graphene FET Model for Circuit Design. IEEE Transactions on Electron Devices, 2014, 61, 1199-1206.	3.0	122
13	Piezoresistive Properties of Suspended Graphene Membranes under Uniaxial and Biaxial Strain in Nanoelectromechanical Pressure Sensors. ACS Nano, 2016, 10, 9879-9886.	14.6	110
14	Schottky-Barrier Height Tuning by Means of Ion Implantation Into Preformed Silicide Films Followed by Drive-In Anneal. IEEE Electron Device Letters, 2007, 28, 565-568.	3.9	100
15	A Comparative Study of Two Different Schemes to Dopant Segregation at NiSi/Si and PtSi/Si Interfaces for Schottky Barrier Height Lowering. IEEE Transactions on Electron Devices, 2008, 55, 396-403.	3.0	98
16	Prevention of Graphene Restacking for Performance Boost of Supercapacitorsâ€”A Review. Crystals, 2013, 3, 163-190.	2.2	98
17	A comparative study of the diffusion barrier properties of TiN and ZrN. Thin Solid Films, 1986, 145, 81-88.	1.8	90
18	Enhanced formation of the C54 phase of TiSi ₂ by an interposed layer of molybdenum. Applied Physics Letters, 1996, 69, 975-977.	3.3	89

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19	A new model for the low-frequency noise and the noise level variation in polysilicon emitter BJTs. IEEE Transactions on Electron Devices, 2002, 49, 514-520.	3.0	89
20	Chemical vapor deposited graphene: From synthesis to applications. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 2439-2449.	1.8	81
21	500 μ C Bipolar Integrated OR/NOR Gate in 4H-SiC. IEEE Electron Device Letters, 2013, 34, 1091-1093.	3.9	80
22	Inkjet Printing of 2D Layered Materials. ChemPhysChem, 2014, 15, 3427-3434.	2.1	78
23	Pressure sensors based on suspended graphene membranes. Solid-State Electronics, 2013, 88, 89-94.	1.4	70
24	Graphene ribbons with suspended masses as transducers in ultra-small nanoelectromechanical accelerometers. Nature Electronics, 2019, 2, 394-404.	26.0	70
25	Reduction of the Schottky barrier height on silicon carbide using Au nano-particles. Solid-State Electronics, 2002, 46, 1433-1440.	1.4	69
26	Graphene-based CO ₂ sensing and its cross-sensitivity with humidity. RSC Advances, 2017, 7, 22329-22339.	3.6	68
27	Humidity and CO ₂ gas sensing properties of double-layer graphene. Carbon, 2018, 127, 576-587.	10.3	66
28	Investigation of aluminum nitride grown by metal-organic chemical-vapor deposition on silicon carbide. Journal of Applied Physics, 1997, 82, 2990-2995.	2.5	65
29	All-solid-state micro-supercapacitors based on inkjet printed graphene electrodes. Applied Physics Letters, 2016, 109, .	3.3	62
30	Thermally stable low ohmic contacts to p-type 6H-SiC using cobalt silicides. Solid-State Electronics, 1996, 39, 1559-1565.	1.4	57
31	Ultradeep, low-damage dry etching of SiC. Applied Physics Letters, 2000, 76, 739-741.	3.3	57
32	Surface-Passivation Effects on the Performance of 4H-SiC BJTs. IEEE Transactions on Electron Devices, 2011, 58, 259-265.	3.0	57
33	Modeling and Characterization of Current Gain Versus Temperature in 4H-SiC Power BJTs. IEEE Transactions on Electron Devices, 2010, 57, 704-711.	3.0	56
34	Design and Characterization of High-Temperature ECL-Based Bipolar Integrated Circuits in 4H-SiC. IEEE Transactions on Electron Devices, 2012, 59, 1076-1083.	3.0	56
35	High-Voltage 4H-SiC PiN Diodes With Etched Junction Termination Extension. IEEE Electron Device Letters, 2009, 30, 1170-1172.	3.9	55
36	Geometrical effects in high current gain 1100-V 4H-SiC BJTs. IEEE Electron Device Letters, 2005, 26, 743-745.	3.9	53

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37	Fully inkjet printed ultrathin microsupercapacitors based on graphene electrodes and a nano-graphene oxide electrolyte. <i>Nanoscale</i> , 2019, 11, 10172-10177.	5.6	49
38	Low resistivity ohmic titanium carbide contacts to n- and p-type 4H-silicon carbide. <i>Solid-State Electronics</i> , 2000, 44, 1179-1186.	1.4	48
39	Comprehensive study on low-frequency noise and mobility in Si and SiGe pMOSFETs with high- κ gate dielectrics and TiN gate. <i>IEEE Transactions on Electron Devices</i> , 2006, 53, 836-843.	3.0	48
40	Bilayer insulator tunnel barriers for graphene-based vertical hot-electron transistors. <i>Nanoscale</i> , 2015, 7, 13096-13104.	5.6	48
41	1200-V 5.2- Ω 4H-SiC BJTs With a High Common-Emitter Current Gain. <i>IEEE Electron Device Letters</i> , 2007, 28, 1007-1009.	3.9	46
42	Manufacture and characterization of graphene membranes with suspended silicon proof masses for MEMS and NEMS applications. <i>Microsystems and Nanoengineering</i> , 2020, 6, 17.	7.0	46
43	A simple route towards high-concentration surfactant-free graphene dispersions. <i>Carbon</i> , 2012, 50, 3113-3116.	10.3	45
44	ICP etching of SiC. <i>Solid-State Electronics</i> , 1998, 42, 2283-2288.	1.4	44
45	Schottky diode formation and characterization of titanium tungsten to n- and p-type 4H silicon carbide. <i>Journal of Applied Physics</i> , 2000, 87, 8039-8044.	2.5	43
46	Percolation thresholds of two-dimensional continuum systems of rectangles. <i>Physical Review E</i> , 2013, 88, 012101.	2.1	43
47	Schottky barrier height dependence on the metal work function for p-type 4H-silicon carbide. <i>Journal of Electronic Materials</i> , 2001, 30, 242-246.	2.2	42
48	1/f noise in Si and Si _{0.7} /Ge _{0.3} pMOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2003, 50, 2513-2519.	3.0	40
49	Graphene transfer methods for the fabrication of membrane-based NEMS devices. <i>Microelectronic Engineering</i> , 2016, 159, 108-113.	2.4	40
50	Formation and characterization of cobalt 6H-silicon carbide Schottky contacts. <i>Applied Physics Letters</i> , 1993, 63, 3069-3071.	3.3	37
51	SB-MOSFETs in UTB-SOI Featuring PtSi Source/Drain With Dopant Segregation. <i>IEEE Electron Device Letters</i> , 2008, 29, 125-127.	3.9	37
52	Bias-temperature instability in single-layer graphene field-effect transistors. <i>Applied Physics Letters</i> , 2014, 105, .	3.3	37
53	Going ballistic: Graphene hot electron transistors. <i>Solid State Communications</i> , 2015, 224, 64-75.	1.9	37
54	15 kV-Class Implantation-Free 4H-SiC BJTs With Record High Current Gain. <i>IEEE Electron Device Letters</i> , 2018, 39, 63-66.	3.9	37

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55	Suspended Graphene Membranes with Attached Silicon Proof Masses as Piezoresistive Nanoelectromechanical Systems Accelerometers. Nano Letters, 2019, 19, 6788-6799.	9.1	36
56	Thin-film growth and compositional effects in YBa ₂ Cu ₃ O _{7-x} layers prepared by metalorganic chemical vapor deposition. Journal of Applied Physics, 1993, 74, 4631-4642.	2.5	35
57	Fabrication of 2700-V 12- Ω Non Ion-Implanted 4H-SiC BJTs With Common-Emitter Current Gain of 50. IEEE Electron Device Letters, 2008, 29, 1135-1137.	3.9	35
58	Temperature stability of cobalt Schottky contacts on n- and p-type 6H silicon carbide. Applied Surface Science, 1993, 73, 316-321.	6.1	34
59	Via-hole etching for SiC. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B: Microelectronics Processing and Phenomena, 1999, 17, 2050.	1.6	34
60	Morphological instabilities of nickel and cobalt silicides on silicon. Applied Surface Science, 1991, 53, 87-91.	6.1	33
61	Lateral encroachment of Ni-silicides in the source/drain regions on ultrathin silicon-on-insulator. Applied Physics Letters, 2005, 86, 253507.	3.3	33
62	Interaction of NiSi with dopants for metallic source/drain applications. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, C111-C1111.	1.2	33
63	Limitation of Ti/TiN diffusion barrier layers in silicon technology. Vacuum, 1985, 35, 547-553.	3.5	32
64	Electrical characterization of TiC ohmic contacts to aluminum ion implanted 4H-silicon carbide. Applied Physics Letters, 2000, 77, 1478-1480.	3.3	32
65	Influence of growth conditions on electrical characteristics of AlN on SiC. Applied Physics Letters, 1997, 70, 3549-3551.	3.3	31
66	Plasma chemistries for high density plasma etching of SiC. Journal of Electronic Materials, 1999, 28, 196-201.	2.2	31
67	Low resistivity ohmic contacts on 4H-silicon carbide for high power and high temperature device applications. Microelectronic Engineering, 2002, 60, 261-268.	2.4	31
68	Reduced self-heating by strained silicon substrate engineering. Applied Surface Science, 2008, 254, 6182-6185.	6.1	31
69	CoSi ₂ ohmic contacts to n-type 6H-SiC. Solid-State Electronics, 1995, 38, 2023-2028.	1.4	29
70	A robust spacer gate process for deca-nanometer high-frequency MOSFETs. Microelectronic Engineering, 2006, 83, 434-439.	2.4	29
71	2.2 kV SiC BJTs with Low $V_{CE(sat)}$; Fast Switching and Short-Circuit Capability. Materials Science Forum, 0, 645-648, 1033-1036.	0.3	29
72	TiSi ₂ /TiN—A Stable Multilayered Contact Structure for Shallow Implanted Junctions in VLSI Technology. Physica Scripta, 1983, 28, 633-636.	2.5	28

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73	CVD-based tungsten carbide schottky contacts to 6H-SiC for very high-temperature operation. Journal of Electronic Materials, 2000, 29, 372-375.	2.2	28
74	Dependence of the colored frequency noise in spin torque oscillators on current and magnetic field. Applied Physics Letters, 2014, 104, 092405.	3.3	28
75	Bipolar integrated circuits in SiC for extreme environment operation. Semiconductor Science and Technology, 2017, 32, 034002.	2.0	28
76	A novel strained Si/sub 0.7/Ge/sub 0.3/ surface-channel pMOSFET with an ALD TiN/Al/sub 2/O/sub 3//HfAlO/sub x//Al/sub 2/O3 gate stack. IEEE Electron Device Letters, 2003, 24, 171-173.	3.9	27
77	Stable dynamic avalanche in Si power diodes. Applied Physics Letters, 1999, 74, 3170-3172.	3.3	26
78	Fabrication and characterization of heterojunction diodes with HVPE-grown GaN on 4H-SiC. IEEE Transactions on Electron Devices, 2001, 48, 444-449.	3.0	26
79	Influence of Emitter Width and Emitter-Base Distance on the Current Gain in 4H-SiC Power BJTs. IEEE Transactions on Electron Devices, 2010, 57, 2664-2670.	3.0	26
80	High-Voltage (2.8 kV) Implantation-Free 4H-SiC BJTs With Long-Term Stability of the Current Gain. IEEE Transactions on Electron Devices, 2011, 58, 2665-2669.	3.0	26
81	Optimizing the optical and electrical properties of graphene ink thin films by laser-annealing. 2D Materials, 2015, 2, 011003.	4.4	26
82	Silicon nitride films deposited from SiH ₂ Cl ₂ -NH ₃ by low pressure chemical vapor deposition: kinetics, thermodynamics, composition and structure. Thin Solid Films, 1992, 213, 182-191.	1.8	25
83	Surface passivation oxide effects on the current gain of 4H-SiC bipolar junction transistors. Applied Physics Letters, 2008, 92, 082113.	3.3	25
84	Effects of Carbon on Schottky Barrier Heights of NiSi Modified by Dopant Segregation. IEEE Electron Device Letters, 2009, 30, 608-610.	3.9	25
85	5.8-kV Implantation-Free 4H-SiC BJT With Multiple-Shallow-Trench Junction Termination Extension. IEEE Electron Device Letters, 2015, 36, 168-170.	3.9	25
86	Arsenic distribution in bilayers of TiSi ₂ on polycrystalline silicon during heat treatment. Thin Solid Films, 1983, 110, 281-289.	1.8	24
87	Strained Si/SiGe MOS technology: Improving gate dielectric integrity. Microelectronic Engineering, 2009, 86, 218-223.	2.4	24
88	RF Performance Projections of Graphene FETs vs. Silicon MOSFETs. ECS Solid State Letters, 2012, 1, Q39-Q41.	1.4	24
89	A manufacturable process integration approach for graphene devices. Solid-State Electronics, 2013, 84, 185-190.	1.4	24
90	Influence of Passivation Oxide Thickness and Device Layout on the Current Gain of SiC BJTs. IEEE Electron Device Letters, 2015, 36, 11-13.	3.9	24

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91	550 Å°C 4H-SiC p-i-n Photodiode Array With Two-Layer Metallization. IEEE Electron Device Letters, 2016, 37, 1594-1596.	3.9	24
92	Wet Transfer of Inkjet Printed Graphene for Microsupercapacitors on Arbitrary Substrates. ACS Applied Energy Materials, 2019, 2, 158-163.	5.1	24
93	Formation of iron disilicide on amorphous silicon. Applied Surface Science, 1991, 53, 153-158.	6.1	23
94	High rate etching of SiC and SiCN in NF ₃ inductively coupled plasmas. Solid-State Electronics, 1998, 42, 743-747.	1.4	23
95	Impact of strain and channel orientation on the low-frequency noise performance of Si n- and pMOSFETs. Solid-State Electronics, 2007, 51, 771-777.	1.4	23
96	Hot-Carrier Degradation and Bias-Temperature Instability in Single-Layer Graphene Field-Effect Transistors: Similarities and Differences. IEEE Transactions on Electron Devices, 2015, 62, 3876-3881.	3.0	23
97	Inductively coupled plasma etch damage in 4H-SiC investigated by Schottky diode characterization. Journal of Electronic Materials, 2001, 30, 247-252.	2.2	22
98	Strain Engineering in GeSnSi Materials. ECS Transactions, 2013, 50, 527-531.	0.5	22
99	500 Å°C High Current 4H-SiC Lateral BJTs for High-Temperature Integrated Circuits. IEEE Electron Device Letters, 2017, 38, 1429-1432.	3.9	22
100	Nickel-enhanced solid-phase epitaxial regrowth of amorphous silicon. Physical Review Letters, 1992, 68, 1872-1875.	7.8	21
101	A low-complexity 62-GHz fT SiGe heterojunction bipolar transistor process using differential epitaxy and in situ phosphorus-doped poly-Si emitter at very low thermal budget. Solid-State Electronics, 2000, 44, 549-554.	1.4	21
102	Characterization of heterojunction diodes with hydride vapor phase epitaxy grown AlGaIn on 4H-SiC. Journal of Applied Physics, 2002, 91, 2372-2379.	2.5	21
103	Random telegraph signal noise in SiGe heterojunction bipolar transistors. Journal of Applied Physics, 2002, 92, 4414-4421.	2.5	21
104	Ferroelectric Pb(Zr _{0.52} Ti _{0.48})/SiC field-effect transistor. Applied Physics Letters, 2003, 83, 3975-3977.	3.3	21
105	Robust, scalable self-aligned platinum silicide process. Applied Physics Letters, 2006, 88, 142114.	3.3	21
106	Carrier transport through a dry-etched InP-based two-dimensional photonic crystal. Journal of Applied Physics, 2007, 101, 123101.	2.5	21
107	Performance Fluctuation of FinFETs With Schottky Barrier Source/Drain. IEEE Electron Device Letters, 2008, 29, 506-508.	3.9	21
108	New method to calibrate the pattern dependency of selective epitaxy of SiGe layers. Solid-State Electronics, 2009, 53, 858-861.	1.4	21

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109	Low-Temperature Annealing of Radiation-Induced Degradation in 4H-SiC Bipolar Junction Transistors. IEEE Electron Device Letters, 2010, 31, 707-709.	3.9	21
110	The performance improvement evaluation for SiGe-based IR detectors. Solid-State Electronics, 2011, 62, 72-76.	1.4	21
111	Scalable Fabrication of 2D Semiconducting Crystals for Future Electronics. Electronics (Switzerland), 2015, 4, 1033-1061.	3.1	21
112	Precise percolation thresholds of two-dimensional random systems comprising overlapping ellipses. Physica A: Statistical Mechanics and Its Applications, 2016, 462, 940-950.	2.6	21
113	Reactive sputtering of titanium boride. Thin Solid Films, 1989, 172, 133-140.	1.8	20
114	High-resolution recoil spectrometry for separate characterization of Ga and As in $\text{Al}_x\text{Ga}(1-x)\text{As}$ structures. Applied Physics Letters, 1992, 60, 219-221.	3.3	20
115	Low-frequency noise and Coulomb scattering in $\text{Si}_{0.8}\text{Ge}_{0.2}$ surface channel pMOSFETs with ALD Al_2O_3 gate dielectrics. Solid-State Electronics, 2005, 49, 907-914.	1.4	20
116	On the electron mobility enhancement in biaxially strained Si MOSFETs. Solid-State Electronics, 2008, 52, 498-505.	1.4	20
117	Ink-jet printed thin-film transistors with carbon nanotube channels shaped in long strips. Journal of Applied Physics, 2011, 109, 084915.	2.5	20
118	Modeling and Characterization of the on-Resistance in 4H-SiC Power BJTs. IEEE Transactions on Electron Devices, 2011, 58, 2081-2087.	3.0	20
119	A 600 °C TTL-based 11-stage Ring Oscillator in Bipolar Silicon Carbide Technology. IEEE Electron Device Letters, 2018, , 1-1.	3.9	20
120	Towards Silicon Carbide VLSI Circuits for Extreme Environment Applications. Electronics (Switzerland), 2019, 8, 496.	3.1	20
121	Dynamic avalanche in 3.3-kV Si power diodes. IEEE Transactions on Electron Devices, 1999, 46, 781-786.	3.0	19
122	Chemical vapor deposition of undoped and in-situ boron- and arsenic-doped epitaxial and polycrystalline silicon films grown using silane at reduced pressure. Journal of Applied Physics, 2000, 88, 1655-1663.	2.5	19
123	Extraction of emitter and base series resistances of bipolar transistors from a single DC measurement. IEEE Transactions on Semiconductor Manufacturing, 2000, 13, 119-126.	1.7	19
124	On Different Process Schemes for MOSFETs With a Controllable NiSi-Based Metallic Source/Drain. IEEE Transactions on Electron Devices, 2011, 58, 1898-1906.	3.0	19
125	A Hysteresis-Free High-k Dielectric and Contact Resistance Considerations for Graphene Field Effect Transistors. ECS Transactions, 2011, 41, 165-171.	0.5	19
126	Thulium Silicate Interfacial Layer for Scalable High-k/Metal Gate Stacks. IEEE Transactions on Electron Devices, 2013, 60, 3271-3276.	3.0	19

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127	Large scale integration of graphene transistors for potential applications in the back end of the line. Solid-State Electronics, 2015, 108, 61-66.	1.4	19
128	Thermal degradation of TiSi ₂ /poly-Si gate electrodes. Thin Solid Films, 1989, 168, 325-334.	1.8	18
129	Modeling the variation of the low-frequency noise in polysilicon emitter bipolar junction transistors. IEEE Electron Device Letters, 2001, 22, 242-244.	3.9	18
130	The influence of band offsets on the IV characteristics for GaN/SiC heterojunctions. Solid-State Electronics, 2002, 46, 827-835.	1.4	18
131	Self-Heating Effects in a BiCMOS on SOI Technology for RFIC Applications. IEEE Transactions on Electron Devices, 2005, 52, 1423-1428.	3.0	18
132	High-Current-Gain SiC BJTs With Regrown Extrinsic Base and Etched JTE. IEEE Transactions on Electron Devices, 2008, 55, 1894-1898.	3.0	18
133	High power devices in wide bandgap semiconductors. Science China Information Sciences, 2011, 54, 1087-1093.	4.3	18
134	SiC Etching and Sacrificial Oxidation Effects on the Performance of 4H-SiC BJTs. Materials Science Forum, 2014, 778-780, 1005-1008.	0.3	18
135	Conductivity modulated on-axis 4H-SiC 10+kV PiN diodes. , 2015, , .		18
136	A quantitative study of oxygen behavior during CrSi ₂ and TiSi ₂ formation. Journal of Applied Physics, 1989, 65, 567-574.	2.5	17
137	Rapid thermal annealing induced reactions of Co/GaAs thin film structures: Studies using mass and energy dispersive recoil spectrometry. Journal of Applied Physics, 1994, 75, 835-843.	2.5	17
138	Control of Self-Heating in Thin Virtual Substrate Strained Si MOSFETs. IEEE Transactions on Electron Devices, 2006, 53, 2296-2305.	3.0	17
139	Threshold of hierarchical percolating systems. Physical Review E, 2012, 85, 021109.	2.1	17
140	Lateral p-n-p Transistors and Complementary SiC Bipolar Technology. IEEE Electron Device Letters, 2014, 35, 428-430.	3.9	17
141	Noninvasive Scanning Raman Spectroscopy and Tomography for Graphene Membrane Characterization. Nano Letters, 2017, 17, 1504-1511.	9.1	17
142	Influence of Humidity on Contact Resistance in Graphene Devices. ACS Applied Materials & Interfaces, 2018, 10, 41738-41746.	8.0	17
143	On contact resistance measurement using four-terminal Kelvin structures in advanced double-polysilicon bipolar transistor processes. IEEE Transactions on Electron Devices, 1994, 41, 1414-1420.	3.0	16
144	Influence of the addition of Co and Ni on the formation of epitaxial semiconducting $\hat{1}^2$ -FeSi ₂ : Comparison of different evaporation methods. Journal of Applied Physics, 1998, 83, 4193-4201.	2.5	16

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145	Effect of annealing on SiC thin films prepared by pulsed laser deposition. Diamond and Related Materials, 1999, 8, 2099-2102.	3.9	16
146	Low-frequency noise in Si _{0.7} Ge _{0.3} surface channel pMOSFETs with ALD HfO ₂ /Al ₂ O ₃ gate dielectrics. Solid-State Electronics, 2004, 48, 2271-2275.	1.4	16
147	Fully Depleted UTB and Trigate N-Channel MOSFETs Featuring Low-Temperature PtSi Schottky-Barrier Contacts With Dopant Segregation. IEEE Electron Device Letters, 2009, 30, 541-543.	3.9	16
148	Fluorine in low-pressure chemical vapor deposited W/Si contact structures: Inclusion and thermal stability. Applied Physics Letters, 1987, 50, 1497-1499.	3.3	15
149	Boron redistribution during formation of nickel silicides. Applied Surface Science, 1991, 53, 147-152.	6.1	15
150	Junction barrier Schottky diodes in 6H SiC. Solid-State Electronics, 1998, 42, 1757-1759.	1.4	15
151	Preparation of AlN thin films by nitridation of Al-coated Si substrate. Thin Solid Films, 1999, 340, 137-139.	1.8	15
152	Ferroelectric thin films on silicon carbide for next-generation nonvolatile memory and sensor devices. Thin Solid Films, 2004, 469-470, 444-449.	1.8	15
153	A novel self-aligned process for platinum silicide nanowires. Microelectronic Engineering, 2006, 83, 2107-2111.	2.4	15
154	Silicon nanowires integrated with CMOS circuits for biosensing application. Solid-State Electronics, 2014, 98, 26-31.	1.4	15
155	New materials for post-Si computing. MRS Bulletin, 2014, 39, 658-662.	3.5	15
156	Conductivity scaling in supercritical percolation of nanoparticles “not a power law. Nanoscale, 2015, 7, 3424-3428.	5.6	15
157	ECL-Based SiC Logic Circuits for Extreme Temperatures. Materials Science Forum, 0, 821-823, 910-913.	0.3	15
158	Dopant redistribution during the solid-phase growth of CrSi ₂ on Si(100). Journal of Applied Physics, 1988, 64, 4187-4193.	2.5	14
159	Electrical evaluation of high-temperature effects on gate oxide integrity in a self-aligned CoSi ₂ MOS process. Applied Surface Science, 1993, 73, 277-279.	6.1	14
160	Formation and High Frequency CV-Measurements of Aluminum / Aluminum Nitride / 6H Silicon Carbide Structures. Materials Research Society Symposia Proceedings, 1996, 423, 667.	0.1	14
161	Ferroelectric Pb(Zr,Ti)O ₃ /Al ₂ O ₃ /4H-SiC diode structures. Applied Physics Letters, 2002, 81, 895-897.	3.3	14
162	Low-Forward-Voltage-Drop 4H-SiC BJTs Without Base Contact Implantation. IEEE Transactions on Electron Devices, 2008, 55, 1907-1911.	3.0	14

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163	High-Deposition-Rate Atomic Layer Deposition of Thulium Oxide from TmCp_3 and H_2O . Journal of the Electrochemical Society, 2013, 160, D538-D542.	2.9	14
164	Static Nonlinearity in Graphene Field Effect Transistors. IEEE Transactions on Electron Devices, 2014, 61, 3001-3003.	3.0	14
165	Effects of carbon pre-silicidation implant into Si substrate on NiSi. Microelectronic Engineering, 2014, 120, 178-181.	2.4	14
166	Integration of $\text{TmSiO}_2/\text{HfO}_2$ Dielectric Stack in Sub-nm EOT High-k/Metal Gate CMOS Technology. IEEE Transactions on Electron Devices, 2015, 62, 934-939.	3.0	14
167	Wafer-Scale Statistical Analysis of Graphene Field-Effect Transistors—Part II: Analysis of Device Properties. IEEE Transactions on Electron Devices, 2017, 64, 3927-3933.	3.0	14
168	An experimental study of the influence of oxygen on silicide formation with tungsten deposited from tungsten hexafluoride. Journal of Applied Physics, 1991, 69, 213-219.	2.5	13
169	Ni ₂ Si nanowires of extraordinarily low resistivity. Applied Physics Letters, 2006, 88, 213103.	3.3	13
170	Improved electrical performance of carbon nanotube thin film transistors by utilizing composite networks. Applied Physics Letters, 2008, 92, .	3.3	13
171	Strain engineering in suspended graphene devices for pressure sensor applications. , 2012, , .		13
172	Area- and efficiency-optimized junction termination for a 5.6 kV SiC BJT process with low ON-resistance. , 2015, , .		13
173	A Wafer-Scale Ni-Salicide Contact Technology on n-Type 4H-SiC. ECS Journal of Solid State Science and Technology, 2017, 6, P197-P200.	1.8	13
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